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## IN THE CLAIMS

1. (previously amended) A method for forming a feature in a substrate, where residue within the feature can be easily removed, the method comprising the steps of:
  - 5 forming an upper sidewall portion of the feature by laser ablation, the upper sidewall portion forming a void in the substrate, where the upper sidewall portion has an upper sidewall angle, and
  - forming a lower sidewall portion of the feature by laser ablation, the lower sidewall portion forming a void in the substrate, where the lower sidewall portion has a lower sidewall angle,
- 10 where the upper sidewall angle of the upper sidewall portion is shallower than the lower sidewall angle of the lower sidewall portion.
2. (original) The method of claim 1, wherein the upper sidewall angle of the upper sidewall portion is from about thirty degrees to about sixty degrees.
3. (original) The method of claim 1, wherein the lower sidewall angle of the lower sidewall portion is from about sixty degrees to about ninety degrees.
4. (original) The method of claim 1, wherein the lower sidewall portion is formed before the upper sidewall portion is formed.
5. (cancelled)
6. (cancelled)
7. (original) The method of claim 1, wherein the feature comprises a blind bore formed in the substrate.
8. (original) The method of claim 1, wherein the upper sidewall portion has a depth of between about four microns and about eight microns.
9. (original) The method of claim 1, wherein the lower sidewall portion has a depth of between about four microns and about eight microns.

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10. (original) The method of claim 1, wherein the feature has a depth of no more than about twelve microns.
11. (original) The method of claim 1, wherein the substrate comprises silicon.
12. (original) A feature formed according to the method of claim 1.
13. (original) An integrated circuit substrate having features formed according to the method of claim 1.
14. (previously amended) A method for forming indicia elements on a substrate, where the indicia elements have a shape that aids in removal of foreign material from the indicia elements on the substrate, the method comprising the steps of:  
5        forming an upper sidewall portion of the indicia elements by laser ablation, the upper sidewall portion forming a void in the substrate, where the upper sidewall portion has an upper sidewall angle,  
      forming a lower sidewall portion of the indicia elements by laser ablation, the lower sidewall portion forming a void in the substrate, where the lower sidewall portion has a lower sidewall angle,  
10        where the upper sidewall angle of the upper sidewall portion is shallower than the lower sidewall angle of the lower sidewall portion, and  
      forming the indicia elements in a pattern to form identifying indicia on the substrate.
15. (original) The method of claim 14, wherein all of the upper sidewall portions of all of the indicia elements are formed prior to forming any of the lower sidewall portions of any of the indicia elements.
16. (original) The method of claim 14, wherein all of the lower sidewall portions of all of the indicia elements are formed prior to forming any of the upper sidewall portions of any of the indicia elements.

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17. (original) The method of claim 14, wherein a preceding one of the indicia elements is completely formed prior to forming a seceding one of the indicia elements.
18. (previously amended) The method of claim 14, wherein:  
the upper sidewall angle of the upper sidewall portion is from about thirty degrees to about sixty degrees,  
the lower sidewall angle of the lower sidewall portion is from about sixty degrees to about ninety degrees,  
5 the upper sidewall portion has a depth of between about four microns and about eight microns,  
the lower sidewall portion has a depth of between about four microns and about eight microns, and  
10 the indicia element is a blind bore formed in the substrate and has a depth of no more than about twelve microns.
19. (original) An integrated circuit substrate having identifying indicia formed according to the method of claim 14.
20. (cancelled)